

# ZXTP25020CFH 20V, SOT23, PNP medium power transistor

# **Summary**

 $BV_{CEO} > -20V$ 

 $BV_{ECO} > -7V$ 

 $I_{C(cont)} = -4A$ 

 $R_{CE(sat)} = 34m\Omega$ 

 $V_{CE(sat)} < -55mV @ 1A$ 

 $P_{D} = 1.25W$ 

Complementary part number ZXTN25020CFH

# **Description**

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

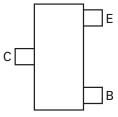
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## **Features**

- · High power dissipation SOT23 package
- · High peak current
- · Low saturation voltage
- · 7V reverse blocking voltage

# **Applications**

- · MOSFET and IGBT gate driving
- · DC DC converters
- · Motor drive
- · High side driver



# Ordering information Pinout - top view

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25020CFHTA	7	8	3,000

# **Device marking**

1B2

# **Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	-25	V
Collector-emitter voltage	V <sub>CEO</sub>	-20	V
Emitter-collector voltage (reverse blocking)	V <sub>ECO</sub>	-7	V
Emitter-base voltage	V <sub>EBO</sub>	-7	V
Continuous collector current <sup>(b)</sup>	I <sub>C</sub>	-4	Α
Peak pulse current	I <sub>CM</sub>	-10	Α
Base current	I <sub>B</sub>	-1	Α
Power dissipation at T <sub>A</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	0.73	W
Linear derating factor		5.84	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(b)</sup>	P <sub>D</sub>	1.05	W
Linear derating factor		8.4	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(c)</sup>	P <sub>D</sub>	1.25	W
Linear derating factor		9.6	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(d)</sup>	P <sub>D</sub>	1.81	W
Linear derating factor		14.5	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

# Thermal resistance

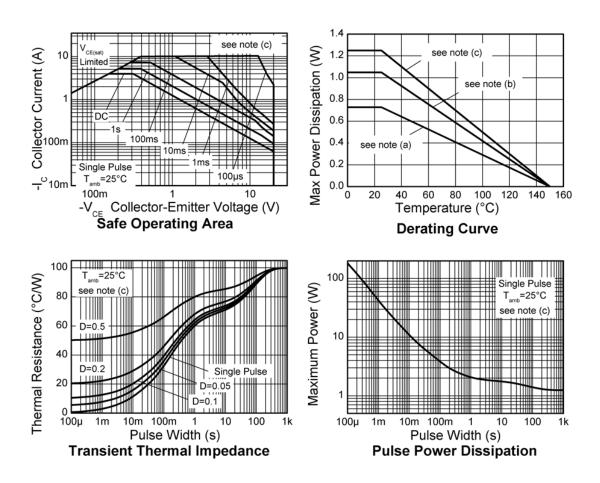
Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	171	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	119	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\Theta JA}$	100	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\Theta JA}$	69	°C/W

### NOTES:

<sup>(</sup>a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

<sup>(</sup>b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

# **Characteristics**



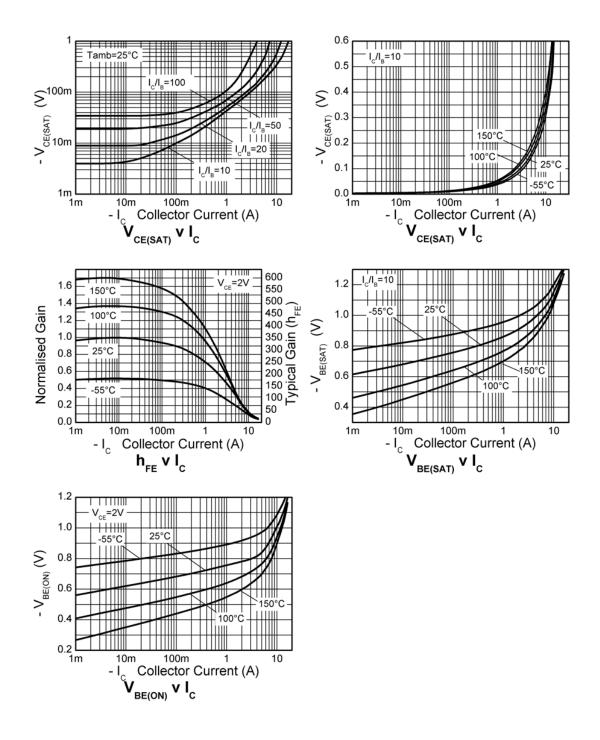
# Electrical characteristics (at $T_{amb} = 25$ °C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	-25	-50		V	I <sub>C</sub> = -100μA
Collector-emitter breakdown voltage (base open)	BV <sub>CEO</sub>	-20	-35		V	I <sub>C</sub> = -10mA <sup>(*)</sup>
Emitter-base breakdown voltage	BV <sub>EBO</sub>	-7	-8.2		V	$I_E = -100 \mu A$
Emitter-collector breakdown voltage (reverse blocking)	BV <sub>ECX</sub>	-7	-8.0		V	$I_E = -100 \mu A^{(*)} R_{BC} < 10 k\Omega$ or $-0.25 < V_{BC} < 0.25 V$
Emitter-collector breakdown voltage (base open)	BV <sub>ECO</sub>	-7	-8.8		V	$I_E = -100 \mu A^{(*)}$
Collector-base cut-off current	I <sub>CBO</sub>		<-1	-50 -20	nA μA	V <sub>CB</sub> = -20V V <sub>CB</sub> = -20V, T <sub>amb</sub> = 100°C
Emitter-base cut-off current	I <sub>EBO</sub>		<-1	-50	nA	V <sub>EB</sub> = -5.6V
Collector-emitter saturation	V <sub>CE(sat)</sub>		-43	-55	mV	$I_C = -1A$ , $I_B = -100 \text{mA}^{(*)}$
voltage			-70	-100	mV	$I_C = -1A$ , $I_B = -20 \text{mA}^{(*)}$
			-120	-170	mV	$I_C = -2A$ , $I_B = -40 \text{mA}^{(*)}$
			-150	-210	mV	$I_C = -4A$ , $I_B = -200 \text{mA}^{(*)}$
Base-emitter saturation voltage	V <sub>BE(sat)</sub>		-930	-1050	mV	$I_C = -4A$ , $I_B = -200 \text{mA}^{(*)}$
Base-emitter turn-on voltage	V <sub>BE(on)</sub>		-810	-900	mV	$I_C = -4A$ , $V_{CE} = -2V^{(*)}$
Static forward current	h <sub>FE</sub>	200	350	500		I <sub>C</sub> = -10mA, V <sub>CE</sub> = -2V <sup>(*)</sup>
transfer ratio		150	250			$I_C = -1A, V_{CE} = -2V^{(*)}$
		85	140			$I_C = -4A$ , $V_{CE} = -2V^{(*)}$
			40			$I_C = -10A$ , $V_{CE} = -2V^{(*)}$
Transition frequency	f <sub>T</sub>		285		MHz	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -10V f = 100MHz
Output capacitance	СОВО		32.4	40	pF	V <sub>CB</sub> = -10V, f = 1MHz <sup>(*)</sup>
Delay time	t <sub>d</sub>		38.4		ns	V <sub>CC</sub> = -15V.
Rise time	t <sub>r</sub>		49.2		ns	I <sub>C</sub> = -750mA,
Storage time	t <sub>s</sub>		168		ns	I <sub>B1</sub> = I <sub>B2</sub> = -15mA
Fall time	t <sub>f</sub>		55		ns	

### NOTES

(\*) Measured under pulsed conditions. Pulse width  ${\leq}300\mu s;$  duty cycle  ${\leq}2\%.$ 

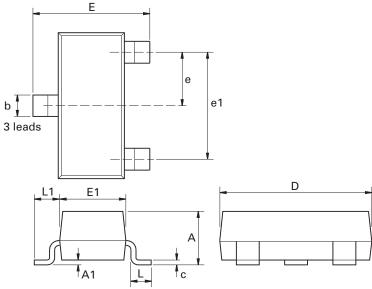
# **Typical characteristics**



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# Package outline - SOT23



Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.037	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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